

## AMENDMENTS

### In the Specification

At p. 1, before the "Technical Field" section insert:

#### -- RELATED PATENT DATA

*A1*  
This patent is a divisional application of U.S. Patent Application Serial No. 08/996,325 which was filed on December 22, 1997, which is a continuation application of U.S. Patent Application Serial No. 08/506,084, filed July 24, 1995 which is now U.S. Patent No. 5,700,727. --

### In the Claims

PLEASE REPEATEDLY  
Please replace the claims with the following clean version of the entire set of pending claims, in accordance with 37 C.F.R. § 1.121(c)(1)(i). Cancel all previous versions of any pending claim.

Add New Claims 69-93 as follows:

*Rule 1.126*  
*sub B1*  
*36*  
*69*  
(New) A thin film transistor comprising:  
a variable thickness thin film transistor layer, the transistor layer having a channel region and one of a source region or a drain region elevationally above the channel region, the one region comprising at least a portion thicker than the channel region; and  
a gate in lateral proximity to the thin film channel region, the gate comprising an annulus which laterally encircles the laterally proximate thin film channel region.